





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
60V	6Ω @ V _{GS} = 5V	220mA

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions

Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM, 1kV CDM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Qsuffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-products/.
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (2N7002AQ)

Mechanical Data

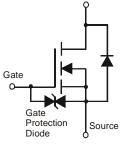
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

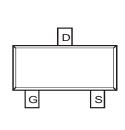
Drain





SOT23





Top View Pin-Out

November 2020

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Top View

Equivalent Circuit

Ordering Information (Note 4)

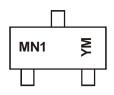
Part Number	Case	Packaging
2N7002A-7	SOT23	3,000/Tape & Reel
2N7002A-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



 $\begin{array}{l} MN1 = Product\ Type\ Marking\ Code \\ YM = Date\ Code\ Marking \\ Y\ or\ \overline{Y} = Year\ (ex:\ H=2020) \\ M\ or\ \overline{M} = Month\ (ex:\ 9=September) \end{array}$

Date Code Key

Year	2008		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	V		Н		J	K	L	М	N	0	Р	R
1												
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 5) V _{GS} = 10V Steady State		T _A = +25°C T _A = +85°C T _A = +100°C	lο	180 130 115	mA
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady State $T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ $T_A = +100^{\circ}C$			lο	220 160 140	mA
Maximum Continuous Body Diode Forward Currer	t (Note 6)	Is	220	mA	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	%)		I _{DM}	800	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Dawer Discipation	(Note 5)	D-	370	mW	
Total Power Dissipation	(Note 6)	PD	540		
Thermal Desigtance Junction to Ambient	(Note 5)	Devi	348		
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	Rejc	91		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Notes:

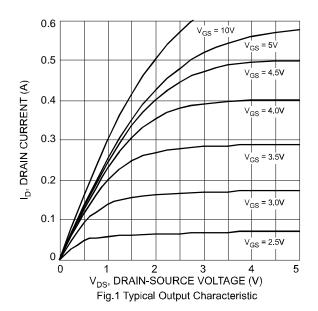
- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

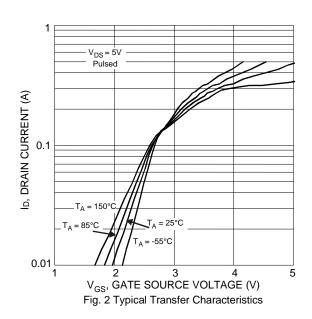


Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)		•		•			
Drain-Source Breakdown Voltage		BVDSS	60	70	_	V	$V_{GS} = 0V$, $I_D = 10\mu A$
Zero Gate Voltage Drain Current @ $T_C = +25^{\circ}C$ @ $T_C = +125^{\circ}C$		IDSS	_	_	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		Igss	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		Vgs(th)	1.2	_	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance @ T _J = +25°C		D		3.5	6		V _G S = 5.0V, I _D = 0.115A
	@ T _J = +125°C	RDS(ON)	_	3.0	5	Ω	$V_{GS} = 10V, I_D = 0.115A$
Forward Transconductance		grs	80	_	_	mS	V _{DS} = 10V, I _D = 0.115A
DYNAMIC CHARACTERISTICS (Note	8)						
Input Capacitance		Ciss	_	23		pF	
Output Capacitance		Coss	_	3.4	_	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Reverse Transfer Capacitance		_	1.4	_	pF	
Gate Resistance		Rg	_	260	400	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
SWITCHING CHARACTERISTICS (No	ote 8)						
Turn-On Delay Time		t _D (ON)	_	10	_	ns	$V_{DD} = 30V$, $I_D = 0.115A$, $R_L = 150\Omega$,
Turn-Off Delay Time		tD(OFF)	_	33	_	ns	$V_{GEN} = 10V, R_{GEN} = 25\Omega$

Notes:





^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.



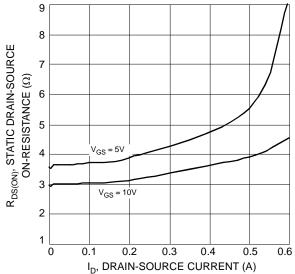


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

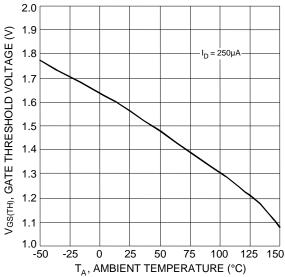


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

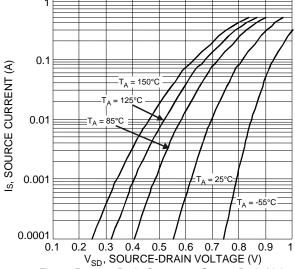


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

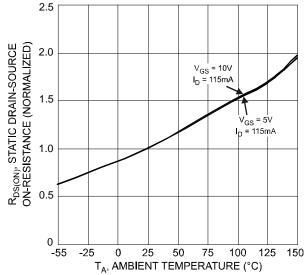
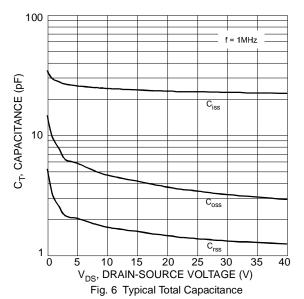


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

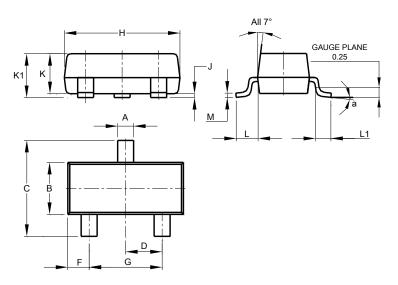




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

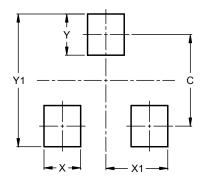


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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